ABSTRACT OF THE DISCLOSURE

An optical proximity correction algorithm using a computer aided design (CAD) system to eliminate the optical proximity effect when transferring the pattern of a photomask onto a

5   wafer. The algorithm comprises, 1. providing an original layout to be formed on the semiconductor wafer, 2. analyzing the image condition of the original layout by the operation of a reverse Fourier transformation method on the original layout, and 3. creating a modified layout to be formed on the photomask according

10   to the image condition.